

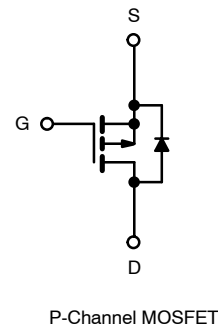
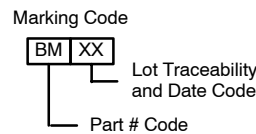
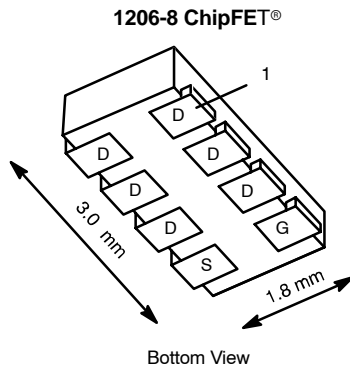


## P-Channel 1.8-V (G-S) MOSFET

| PRODUCT SUMMARY     |                                  |                    |                      |
|---------------------|----------------------------------|--------------------|----------------------|
| V <sub>DS</sub> (V) | r <sub>DS(on)</sub> (Ω)          | I <sub>D</sub> (A) | Q <sub>g</sub> (Typ) |
| -8                  | 0.033 @ V <sub>GS</sub> = -4.5 V | -7.1               | 14                   |
|                     | 0.043 @ V <sub>GS</sub> = -2.5 V | -6.2               |                      |
|                     | 0.060 @ V <sub>GS</sub> = -1.8 V | -5.3               |                      |

### FEATURES

- TrenchFET® Power MOSFET



Ordering Information: Si5445BDC-T1—E3

| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED) |                                   |                       |              |      |   |
|---|-----------------------------------|-----------------------|--------------|------|---|
| Parameter   | Symbol                            | 5 secs                | Steady State | Unit |   |
| Drain-Source Voltage  | V <sub>DS</sub>                   | -8                    |              | V    |   |
| Gate-Source Voltage   | V <sub>GS</sub>                   | ±8                    |              |      |   |
| Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>a</sup>          | I <sub>D</sub>                    | T <sub>A</sub> = 25°C | -7.1         | -5.2 | A |
|   |                                   | T <sub>A</sub> = 85°C | -5.2         | -3.7 |   |
| Pulsed Drain Current  | I <sub>DM</sub>                   | ±20                   |              |      |   |
| Continuous Source Current <sup>a</sup>                                  | I <sub>S</sub>                    | -2.1                  | -1.1         |      |   |
| Maximum Power Dissipation <sup>a</sup>                                  | P <sub>D</sub>                    | T <sub>A</sub> = 25°C | 2.5          | 1.3  | W |
|   |                                   | T <sub>A</sub> = 85°C | 1.3          | 0.7  |   |
| Operating Junction and Storage Temperature Range                        | T <sub>J</sub> , T <sub>stg</sub> | -55 to 150            |              | °C   |   |
| Soldering Recommendations (Peak Temperature) <sup>b, c</sup>            |                                   | 260                   |              |      |   |

| THERMAL RESISTANCE RATINGS               |                   |              |         |      |      |
|--|-------------------|--------------|---------|------|------|
| Parameter                                | Symbol            | Typical      | Maximum | Unit |      |
| Maximum Junction-to-Ambient <sup>a</sup> | R <sub>thJA</sub> | t ≤ 5 sec    | 45      | 50   | °C/W |
|  |                   | Steady State | 85      | 95   |      |
| Maximum Junction-to-Foot (Drain)         | R <sub>thJF</sub> | 17           | 20      |      |      |

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

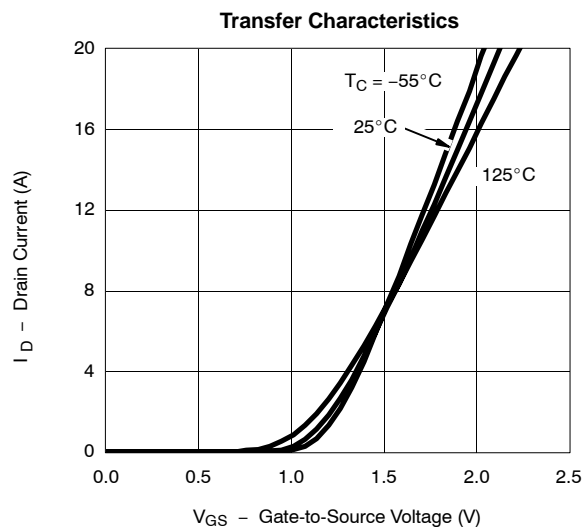
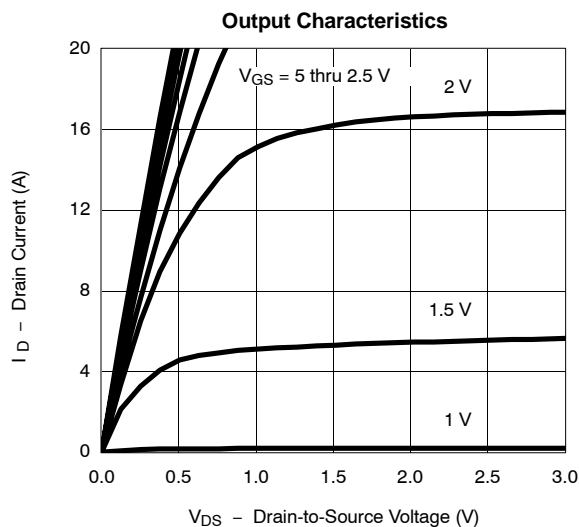
| Parameter                                     | Symbol              | Test Condition   | Min   | Typ   | Max   | Unit |
|---|---------------------|--|-------|-------|-------|------|
| <b>Static</b>                                 |                     |  |       |       |       |      |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA   | -0.45 |       | -1.0  | V    |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±8 V  |       |       | ±100  | nA   |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> = -8 V, V <sub>GS</sub> = 0 V  |       |       | -1    | μA   |
|   |                     | V <sub>DS</sub> = -8 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85°C   |       |       | -5    |      |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>  | V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -4.5 V   | -20   |       |       | A    |
| Drain-Source On-State Resistance <sup>a</sup> | r <sub>DS(on)</sub> | V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -5.2 A  |       | 0.027 | 0.033 | Ω    |
|   |                     | V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -4.5 A  |       | 0.035 | 0.043 |      |
|   |                     | V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -1.7 A  |       | 0.050 | 0.060 |      |
| Forward Transconductance <sup>a</sup>         | g <sub>fs</sub>     | V <sub>DS</sub> = -5 V, I <sub>D</sub> = -5.2 A  |       | 18    |       | S    |
| Diode Forward Voltage <sup>a</sup>            | V <sub>SD</sub>     | I <sub>S</sub> = -1.1 A, V <sub>GS</sub> = 0 V   |       | -0.8  | -1.2  | V    |
| <b>Dynamic<sup>b</sup></b>                    |                     |  |       |       |       |      |
| Total Gate Charge                             | Q <sub>g</sub>      | V <sub>DS</sub> = -4 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -5.2 A  |       | 14    | 21    | nC   |
| Gate-Source Charge                            | Q <sub>gs</sub>     |  | 1.8   |       |       |      |
| Gate-Drain Charge                             | Q <sub>gd</sub>     |  | 3.3   |       |       |      |
| Gate Resistance                               | R <sub>g</sub>      | f = 1 MHz  |       | 8     |       | Ω    |
| Turn-On Delay Time                            | t <sub>d(on)</sub>  | V <sub>DD</sub> = -4 V, R <sub>L</sub> = 4 Ω<br>I <sub>D</sub> ≈ -1 A, V <sub>GEN</sub> = -4.5 V, R <sub>g</sub> = 6 Ω |       | 12    | 20    | ns   |
| Rise Time                                     | t <sub>r</sub>      |  | 22    | 35    |       |      |
| Turn-Off Delay Time                           | t <sub>d(off)</sub> |  | 75    | 115   |       |      |
| Fall Time                                     | t <sub>f</sub>      |  | 50    | 75    |       |      |
| Source-Drain Reverse Recovery Time            | t <sub>rr</sub>     | I <sub>F</sub> = -1.1 A, di/dt = 100 A/μs  |       | 75    | 115   |      |
| Reverse Recovery Charge                       | Q <sub>rr</sub>     |  |       | 40    | 60    | nC   |

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

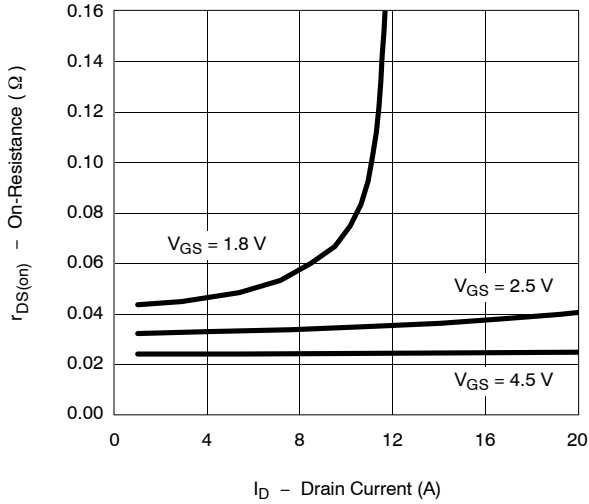
**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



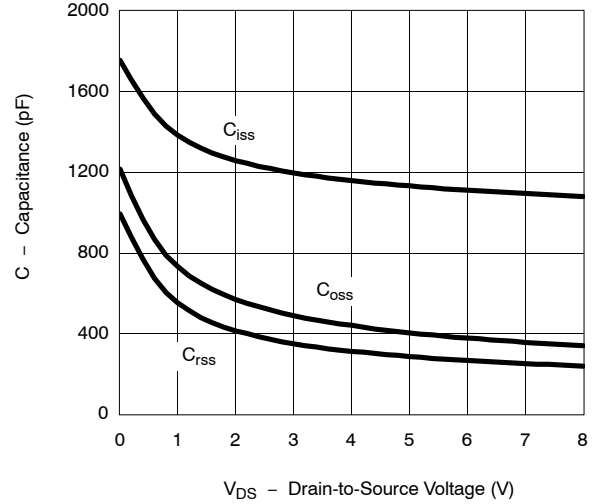


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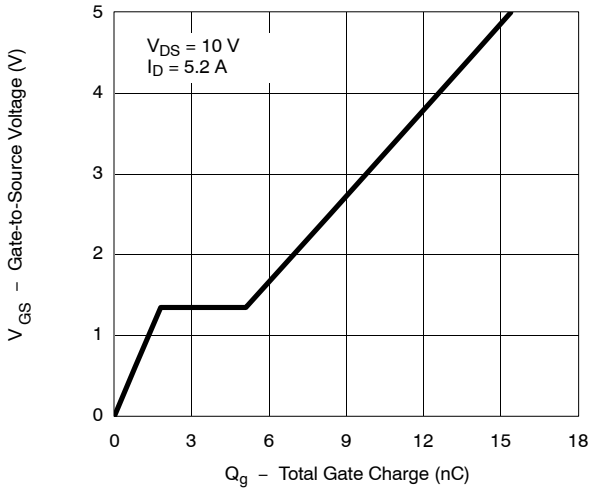
On-Resistance vs. Drain Current



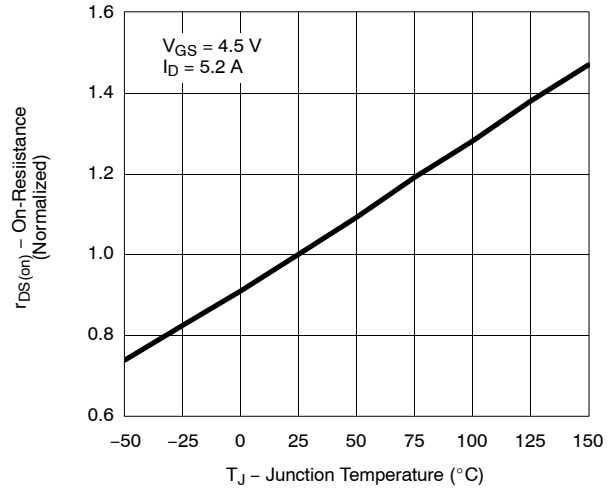
Capacitance



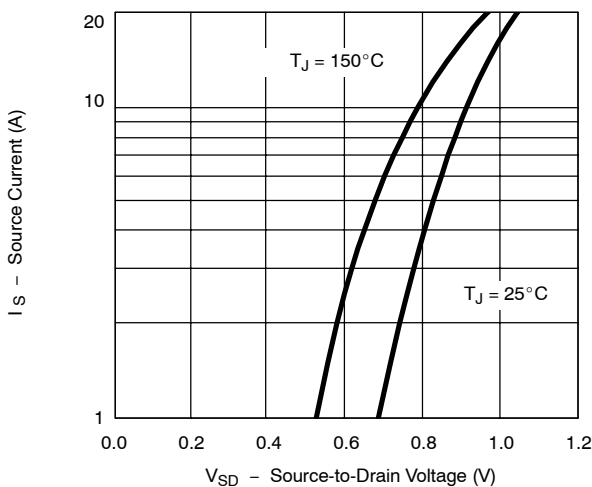
Gate Charge



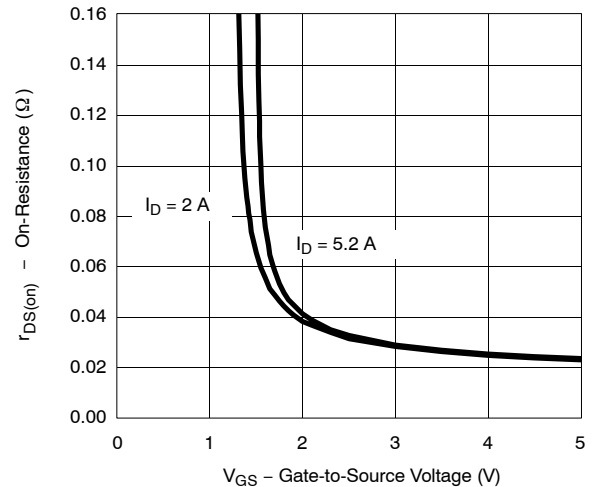
On-Resistance vs. Junction Temperature



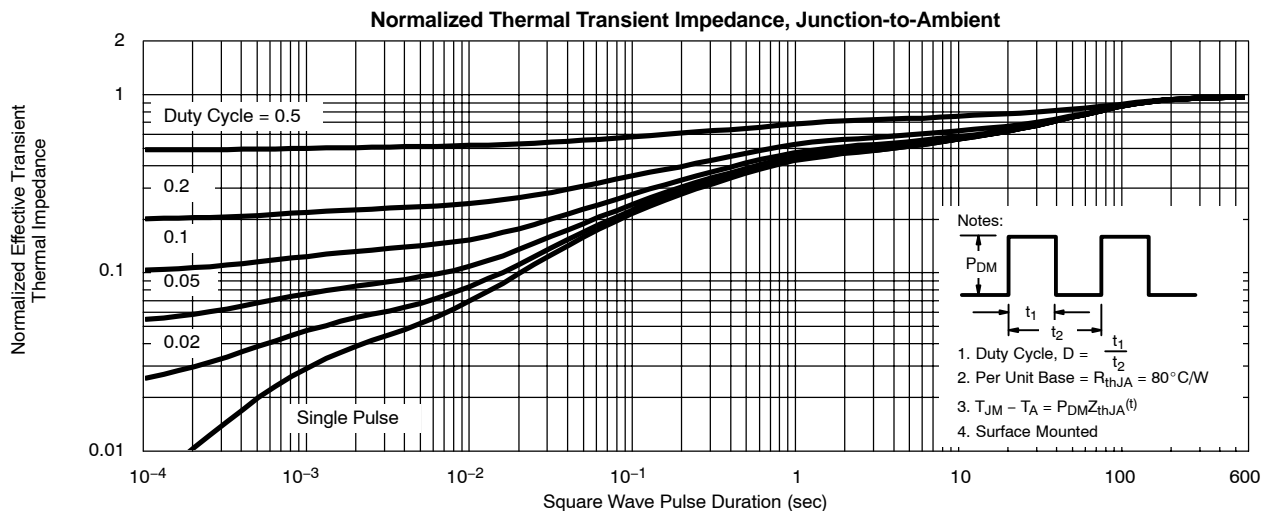
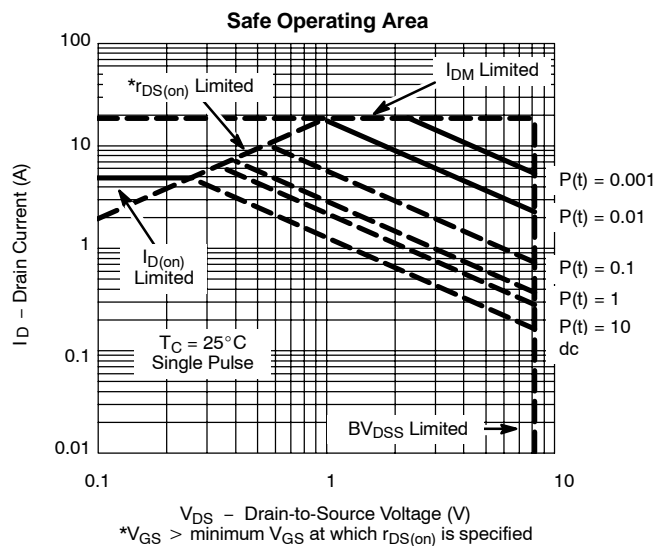
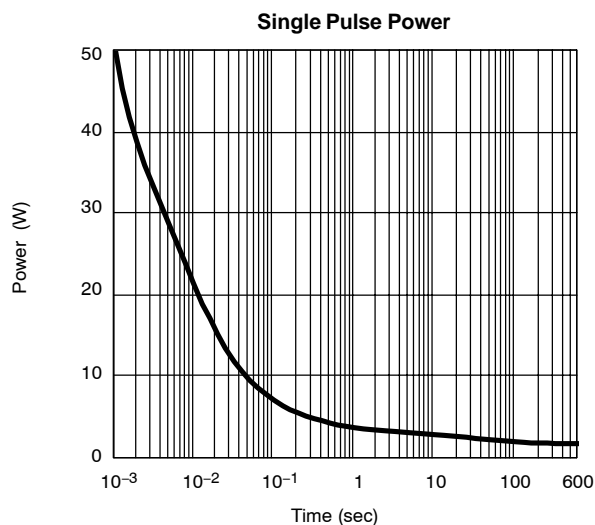
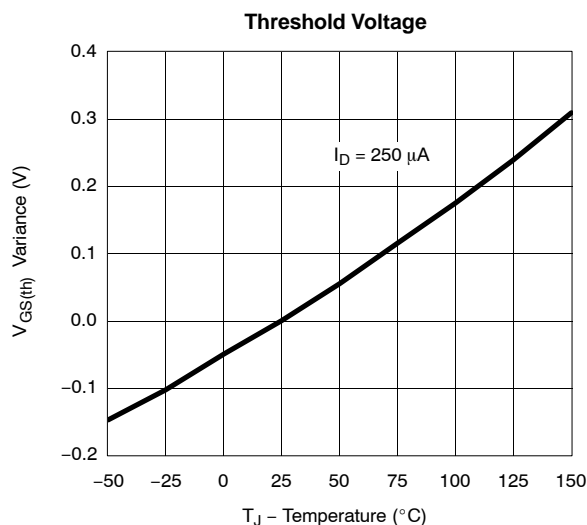
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

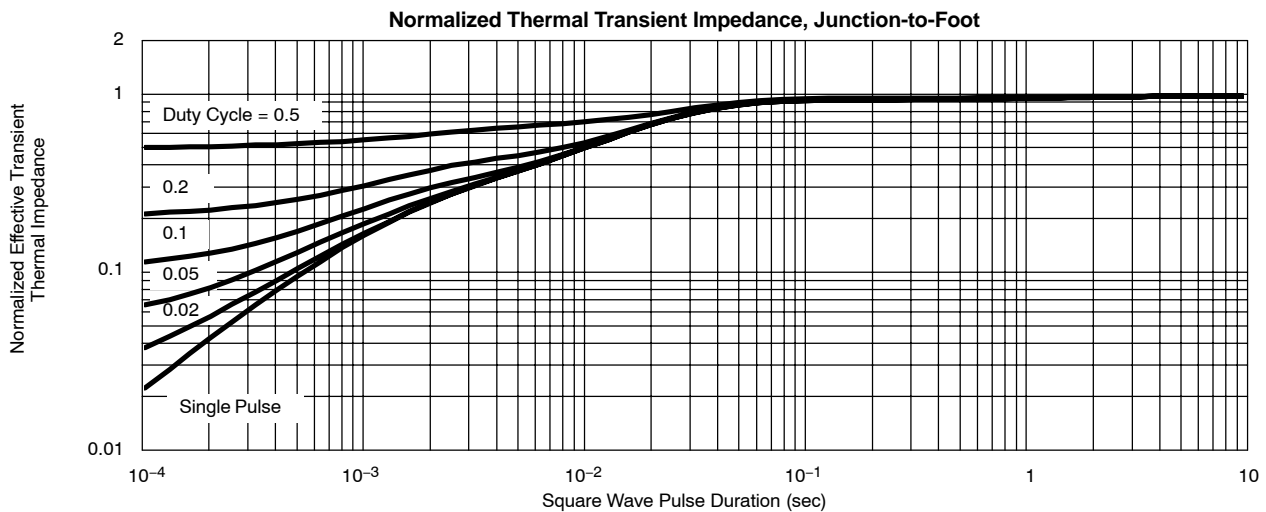


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